

## EAST Search History

| Ref # | Hits | Search Query   | DBs   | Default Operator | Plurals | Time Stamp       |
|-------|------|--|---|------------------|---------|------------------|
| L1    | 10   | (semiconductor adj substrate) and ((film or layer) with (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint                                     | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/03/28 14:29 |
| L2    | 1    | (semiconductor adj substrate) and ((film or layer) near (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint                                     | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/03/28 14:26 |
| L3    | 26   | (semiconductor adj substrate) and ((film or layer) and (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint                                      | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/03/28 14:26 |
| L4    | 9    | (semiconductor adj substrate) and ((film or layer) with (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and intensit\$4                     | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/03/28 14:37 |
| L5    | 13   | (semiconductor adj substrate) and ((film or layer) and (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and intensit\$4                      | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/03/28 14:30 |
| L6    | 8    | (semiconductor adj substrate) and ((film or layer) with (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and intensit\$4 and @ad<="20040129" | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/03/28 14:42 |
| L7    | 1    | (semiconductor adj substrate) and ((film or layer) near (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and intensit\$4 and @ad<="20040129" | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/03/28 14:39 |
| L8    | 12   | (semiconductor adj substrate) and ((film or layer) and (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and intensit\$4 and @ad<="20040129"  | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/03/28 14:39 |

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|     |    |   |   |    |    |                  |
|-----|----|---|---|----|----|------------------|
| L9  | 1  | (semiconductor adj substrate) and ((film or layer) with (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and luminous and intensit\$4 and @ad<="20040129" | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/03/28 14:43 |
| L10 | 3  | (semiconductor adj substrate) and ((film or layer) and (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and luminous and intensit\$4 and @ad<="20040129"  | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/03/28 14:43 |
| S1  | 1  | (film or layer) with (dry adj etch\$5) with (plasma adj emis\$4) with wavelength with endpoint  | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/09/29 14:28 |
| S2  | 2  | (film or layer) same (dry adj etch\$5) same (plasma adj emis\$4) same wavelength same endpoint  | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/09/29 14:28 |
| S3  | 18 | (film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint  | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/10/12 07:07 |
| S4  | 50 | (film or layer) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and wavelength and endpoint   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/10/12 07:12 |
| S5  | 1  | (film or layer) with (dry adj etch\$5) with (plasma adj (emis\$4 or discharg\$4)) with wavelength with endpoint   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/09/29 14:29 |
| S6  | 4  | (film or layer) same (dry adj etch\$5) same (plasma adj (emis\$4 or discharg\$4)) same wavelength same endpoint   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/09/29 14:29 |

## EAST Search History

|     |      |  |   |    |     |                  |
|-----|------|--|---|----|-----|------------------|
| S7  | 1763 | (438/706).CCLS.  | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/10/06 14:01 |
| S8  | 1770 | (438/706).CCLS.  | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/10/06 14:01 |
| S9  | 1    | (film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint and ("SiCN") and ("SiON")                     | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/10/12 07:09 |
| S10 | 0    | 438/706,5.ccls. and (film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint and ("SiCN") and ("SiON") | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/10/12 07:10 |
| S11 | 1    | "438"/\$.ccls. and (film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint and ("SiCN") and ("SiON")  | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/10/12 07:10 |
| S12 | 0    | "257"/\$.ccls. and (film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint and ("SiCN") and ("SiON")  | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/10/12 07:10 |
| S13 | 1    | semiconductor and (film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint and ("SiCN") and ("SiON")   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/10/12 07:11 |
| S14 | 1    | semiconductor and (film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint and (("SiCN") or ("SiON"))  | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/10/12 07:11 |

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|     |     |  |   |    |     |                  |
|-----|-----|--|---|----|-----|------------------|
| S15 | 1   | (film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint and (("SiCN") or ("SiON"))                    | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/10/12 07:11 |
| S16 | 6   | ((("5668019") or ("6514375") or ("5946082") or ("5450205") or ("5362356") or ("5322590")).PN.  | USPAT   | OR | OFF | 2005/10/12 08:55 |
| S17 | 1   | (film or layer) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and wavelength and endpoint and ("SiCN") and ("SiON")    | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/10/12 07:12 |
| S18 | 1   | (film or layer) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and wavelength and endpoint and (("SiCN") or ("SiON"))   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/10/12 07:22 |
| S19 | 1   | ((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and wavelength and endpoint | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/10/12 07:23 |
| S20 | 915 | ((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5)   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/10/12 07:23 |
| S21 | 19  | ((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4))                             | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/10/12 07:38 |
| S22 | 13  | ((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5) and wavelength and endpoint   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/10/12 07:36 |

## EAST Search History

|     |    |   |   |    |     |                  |
|-----|----|---|---|----|-----|------------------|
| S23 | 1  | ((("SiCN") or ("SiON"))) adj (film or layer)) and (dry adj etch\$5) and wavelength and endpoint and (plasma adj (emis\$4 or discharg\$4)) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/10/12 07:35 |
| S24 | 11 | ((("SiCN") or ("SiON"))) adj (film or layer)) and (dry adj etch\$5) and wavelength and endpoint and plasma                                | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/10/12 07:38 |
| S25 | 6  | ((("SiCN") or ("SiON"))) adj (film or layer)) and (dry adj etch\$5) and wavelength and endpoint and plasma and (emis\$4 or discharg\$4)   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/10/12 07:37 |
| S26 | 19 | ((("SiCN") or ("SiON"))) adj (film or layer)) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and plasma                  | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/10/12 07:39 |
| S27 | 2  | ((("SiCN") or ("SiON"))) adj (film or layer)) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and plasma and wavelength   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/10/12 07:40 |
| S28 | 1  | ((("SiCN") or ("SiON"))) adj (film or layer)) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint     | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/03/28 14:24 |
| S29 | 2  | ((("5668019") or ("6703285"))).PN.  | USPAT   | OR | OFF | 2005/10/12 08:55 |